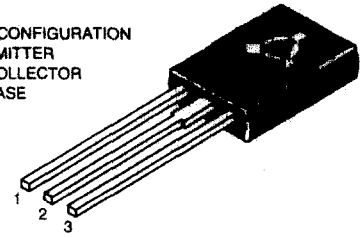
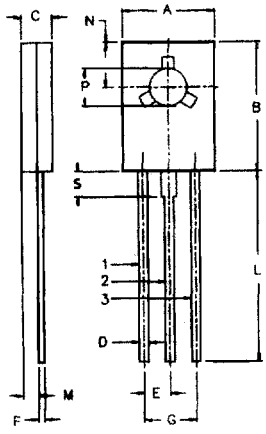
CSA715 PNP PLASTIC POWER TRANSISTOR

Complementary to CSC1162

Low frequency Power Amplifier

PIN CONFIGURATION
1. EMITTER
2. COLLECTOR
3. BASE





DIM	MIN.	MAX.
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 TYP.	
F	0.49	0.75
G	4.5 TYP.	
L	15.7 TYP.	
M	1.27 TYP.	
N	3.75 TYP.	
P	3.0	3.2
S	2.5 TYP.	

ALL DIMENSIONS IN MM

ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	V_{CBO}	max.	35 V
Collector-emitter voltage (open base)	V_{CEO}	max.	35 V
Collector current	I_C	max.	2.5 A
Total power dissipation up to T_C = 25°C	P_{tot}	max.	10 W
Junction temperature	T_j	max.	150 °C
Collector-emitter saturation voltage			
I_C = 2 A; I_B = 0.2 A	V_{CEsat}	max.	1.0 V
D.C. current gain			
I_C = 0.5 A; V_{CE} = 2 V	h_{FE}	min.	60
		max.	320

RATINGS (at T_A=25°C unless otherwise specified)

Limiting values			
Collector-base voltage (open emitter)	V_{CBO}	max.	35 V
Collector-emitter voltage (open base)	V_{CEO}	max.	35 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5.0 V
Collector current	I_C	max.	2.5 A

Collector current (Peak value)	I_C	max.	3 A
Total power dissipation up to T_A = 25°C	P_{tot}	max.	0.75 W
Total power dissipation up to T_C = 25°C	P_{tot}	max.	10 W
Junction temperature	T_j	max.	150 °C
Storage temperature	T_{stg}	−65 to +150	°C

CHARACTERISTICS

T_{amb} = 25°C unless otherwise specified

Collector cutoff current			
I_E = 0; V_{CB} = 35 V	I_{CBO}	max.	20 µA
Breakdown voltages			
I_C = 10 mA; I_B = 0	V_{CEO}	min.	35 V
I_C = 1 mA; I_E = 0	V_{CBO}	min.	35 V
I_E = 1 mA; I_C = 0	V_{EBO}	min.	5 V
Saturation voltage			
I_C = 2 A; I_B = 0.2 A	V_{CEsat}	max.	1.0 V
Base-emitter on voltage			
I_C = 1.5 A; V_{CE} = 2 V	$V_{BE(on)}$	max.	1.5 V
D.C. current gain			
I_C = 0.5 A; V_{CE} = 2 V**	h_{FE}	min.	60
		max.	320
I_C = 1.5 A; V_{CE} = 2 V (Pulse)	h_{FE}	min.	20
Transition frequency			
I_C = 0.2 A; V_{CE} = 2 V	f_T	typ.	160 MHz

** **h_{FE} classification: B: 60-120 C: 100-200 D: 160-320**